MURJ1620CT

Rev.E Mar.-2016

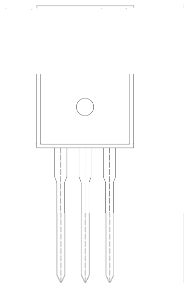
DATA SHEET

TO-220S

Ultrafast Recovery Diode in a TO-220S Plastic Package.

Silicon epitaxial process to produce ultrafast recovery diode with low reverse leakage current and high reliability.

For high frequency, high voltage, high current rectifier diode, freewheeling diode.

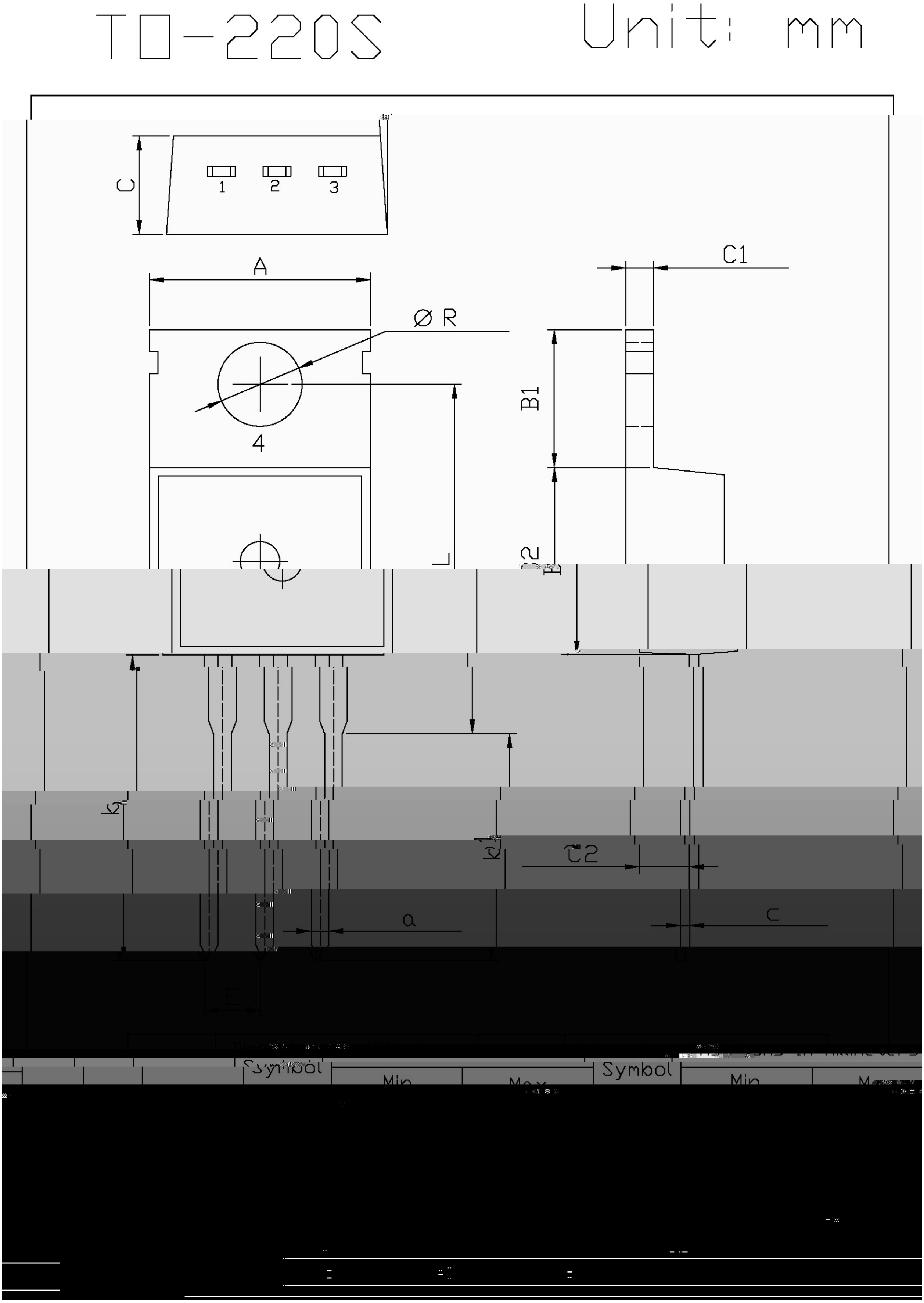


PIN1 Anode PIN 2 Cathode PIN 3 Anode PIN 4 NC

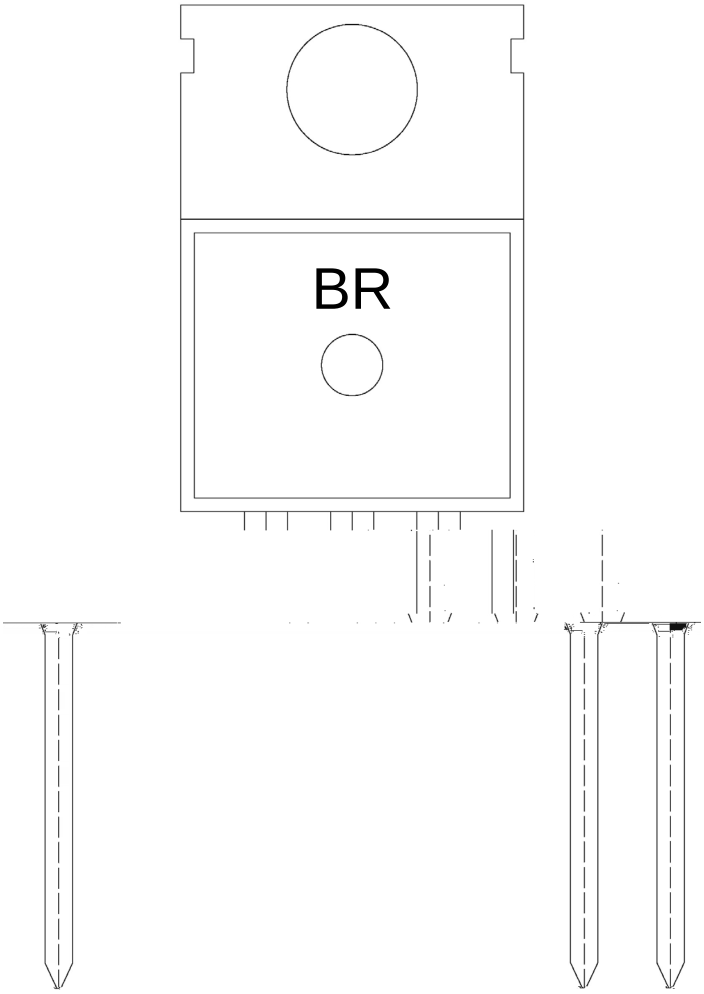
Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	200	V
RMS Voltage	V_{RMS}	140	V
DC Blocking Voltage	V_{DC}	200	V
Average Rectified Forward Current	I_F	2×8	A
Non Repetitive Peak Surge Current	I_{FSM}	120	A
Thermal Resistance Junction to Case	R_{Jc}	2.9	/W
Junction Temperature Range	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions		Min	Typ	Max	Unit
Forward Voltage	V_F	I_F=2A	Tc=25		0.80		V
		I_F=2A	Tc=125		0.66		V
		I_F=8A	Tc=25		0.93	1	V
		I_F=8A	Tc=125		0.82	0.9	V
Instantaneous Reverse Current	I_R Note 1						

/ Package Dimensions



/ Marking Instructions



Note:

BR:	Company Code
MURJ1620	Product Type.
CT:	Internal Structure
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)

Note:

1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 255 5 5 0.5sec;	2.Peak Temp.:255 5 , Duration:5 0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ TUBE

Package Type	Units					Dimension (unit mm^3)		

/ Notices